

### ■ Features

- Wide Bandgap SiC MOSFET Technology.
- Low On-Resistance with High Blocking Voltage.
- Low Capacitances with High-Speed Switching.
- Low Reverse Recovery (Qrr).
- Easy to Parallel and Simple to Drive.
- Robust against Parasitic Turn on Even 0V Turn off Gate Voltage.

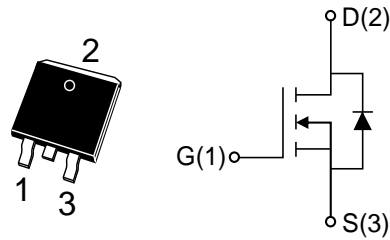
Parameter	Value	Unit
$V_{DS}$	650	V
$R_{DS(on\_typ@VGS=18V)}$	380	mΩ
$I_{D@VGS=15V,TC=25^{\circ}C}$	9.3	A

### ■ Benefits

- Reduced Switching Losses.
- Increased System Switching Frequency.
- Increased Power Density.
- Reduction of Heat Sink Requirements.
- Reduced EMI.

### ■ Application

- Switch Mode Power Supplies.
- High Voltage DC/DC Converters.
- Battery Chargers.
- Motor Drives.
- Pulsed Power Applications.



TO-263M-2L



### Maximum ratings( $T_j=25^{\circ}C$ , Unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Drain to Source Voltage	$V_{DS,max}$	$V_{GS}=0V, I_D=500\mu A$	650	V
Gate to Source Voltage	$V_{GS,max}$	Absolute Maximum Values	-10/+22	V
Recommended Operation Voltage of Gate to Source	$V_{GS,op}$	Recommended Operational Values	0/+18	V
Continuous Drain Current	$I_D$	$V_{GS}=15V, TC=25^{\circ}C$	9.3	A
		$V_{GS}=15V, TC=175^{\circ}C$	6.6	A
Pulsed Drain Current	$I_{D(pulsed)}$	$V_{GS}=15V, TC=25^{\circ}C$	19	A
Power Dissipation	$P_{tot}$	$TC=25^{\circ}C, T_j=175^{\circ}C$	75	W
Operating and Storage Temperature	$T_j, T_{stg}$	—	-55 to+175	$^{\circ}C$



### Thermal Characteristics

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	—	2	—	$^{\circ}C/W$

### Electrical Characteristics

#### Static Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=1.3mA, T_j=25^{\circ}C$	2.7	—	4.5	V
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=500\mu A$	650	—	—	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=650V, T_j=25^{\circ}C$	—	—	10	$\mu A$
Gate to Source Leakage Current	$I_{GSS+}$	$V_{GS}=22V, V_{DS}=0V, T_j=25^{\circ}C$	—	—	250	nA
	$I_{GSS-}$	$V_{GS}=-10V, V_{DS}=0V, T_j=25^{\circ}C$	—	—	-250	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=3.6A, T_j=25^{\circ}C$	—	580	720	m $\Omega$
		$V_{GS}=15V, I_D=3.6A, T_j=175^{\circ}C$	—	460	—	m $\Omega$
		$V_{GS}=18V, I_D=3.6A, T_j=25^{\circ}C$	—	380	550	m $\Omega$
		$V_{GS}=18V, I_D=3.6A, T_j=175^{\circ}C$	—	430	—	m $\Omega$



### Electrical Characteristics

#### Dynamic Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Input Capacitance	$C_{iss}$	VGS=0V, VDS=500V, f=100KHz, Tj=25°C	—	190	—	pF
Output Capacitance	$C_{oss}$		—	15	—	pF
Reverse Transfer Capacitance	$C_{rss}$		—	1.65	—	pF
Gate-Source Charge	$Q_{gs}$	VGS=0/15V, VDS=500V, ID=3.6A, Tj=25°C	—	9.5	—	nC
Gate-Drain Charge	$Q_{gd}$		—	3	—	nC
Total Gate Charge	$Q_g$		—	27	—	nC
Gate Resistance	$R_g$	VAC=25mV, f=1MHz	—	7.5	—	$\Omega$

#### Switching Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Turn-On Delay Time	$t_{d(on)}$	VGS=0/18V, VDD=500V, ID=3.6A, Rg=10 $\Omega$	—	15	—	ns
Rise Time	$t_r$		—	39	—	ns
Turn-Off Delay Time	$t_{d(off)}$		—	16	—	ns
Fall Time	$t_f$		—	69	—	ns

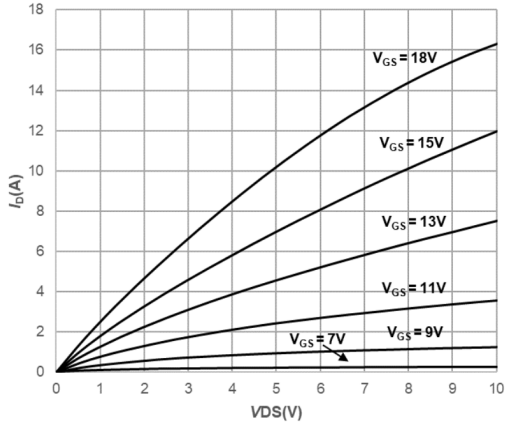
#### Reverse Diode Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Diode Forward Voltage	$V_{SD}$	VGS=0V, ISD=2.1A, Tj=25°C	—	4.5	—	V
Continuous Diode Forward Current	$I_S$	VGS=0V, Tj=25°C	—	7	—	A
Reverse Recovery Time	$t_{rr}$	VGS=0V, ISD=3.6A, VR=500V, di/dt=850A/us, Tj=25°C	—	11	—	ns
Reverse Recovery Charge	$Q_{rr}$		—	35	—	nC
Peak Reverse Recovery Current	$I_{rrm}$		—	5.5	—	A

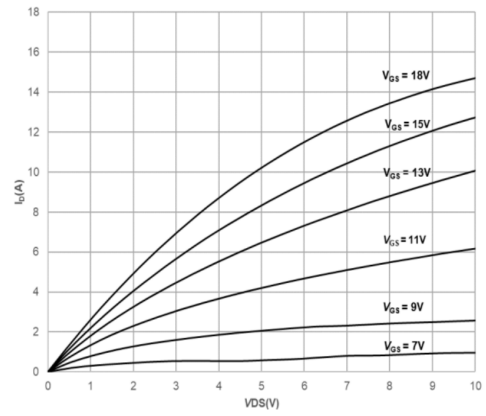


## Typical Performance

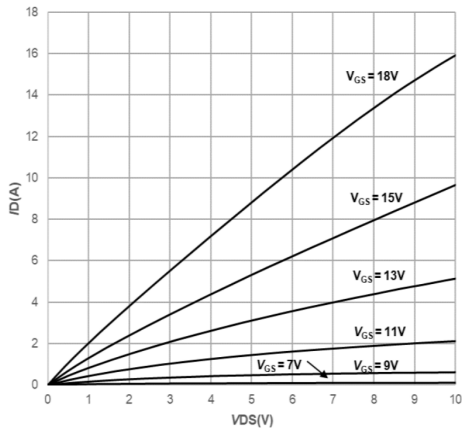
**Fig1. Output Characteristics  $T_j=25^\circ\text{C}$**



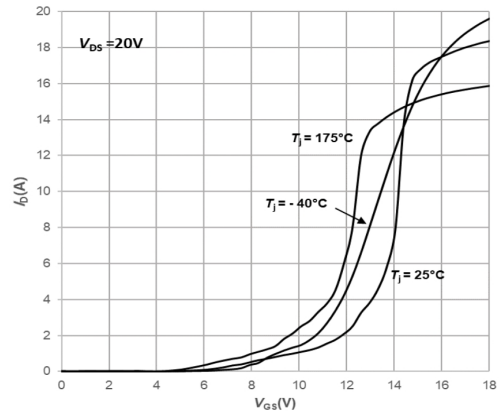
**Fig2. Output Characteristics  $T_j=175^\circ\text{C}$**



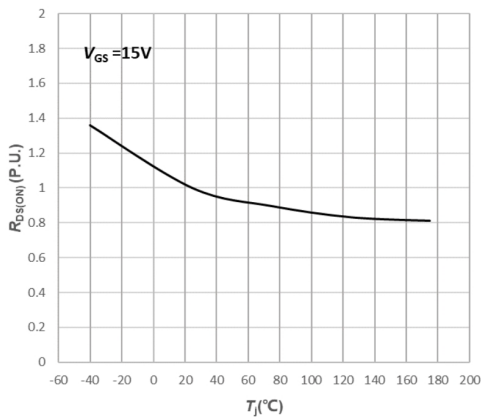
**Fig3. Output Characteristics  $T_j= -40^\circ\text{C}$**



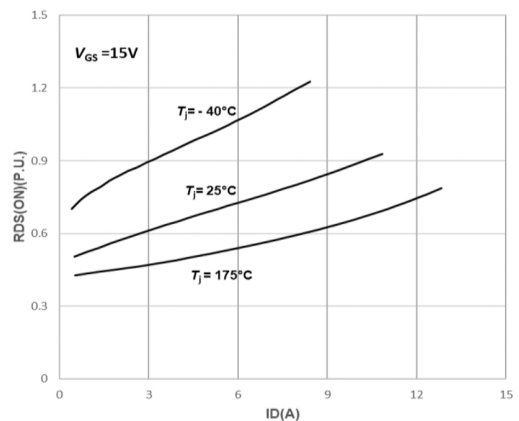
**Fig4. Typical Transfer Characteristics**



**Fig5. Normalized On-Resistance vs. Temperature**

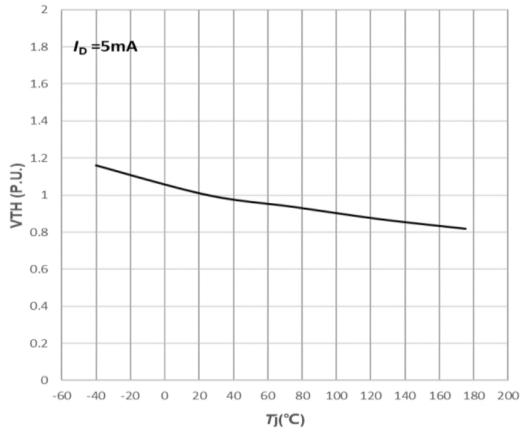


**Fig6. Normalized On-Resistance vs. Drain Current For Various Temperatures**

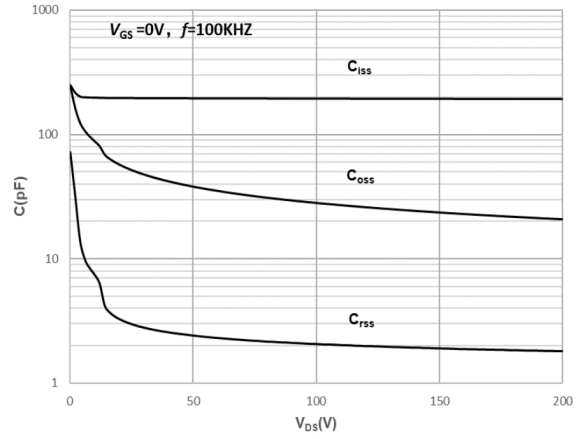


**Typical Performance**

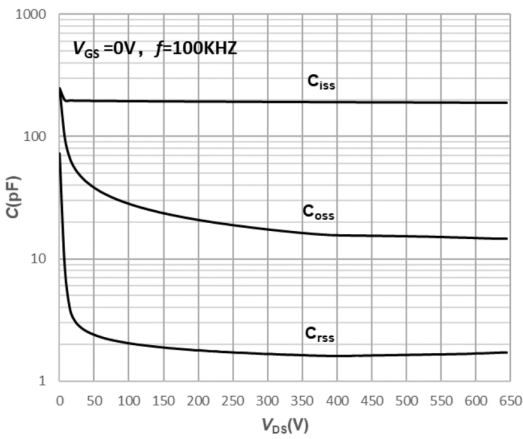
**Fig7. Normalized Threshold Voltage vs. Temperature**



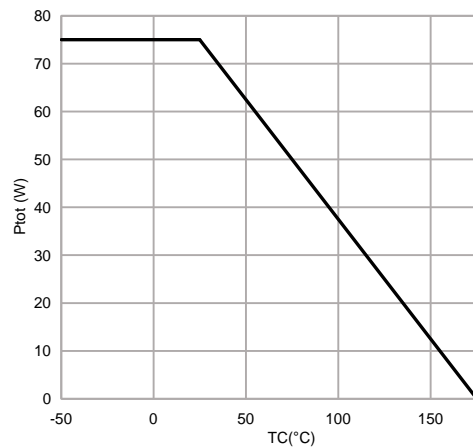
**Fig8. Capacitances vs. Drain-Source Voltage (0-200V)**



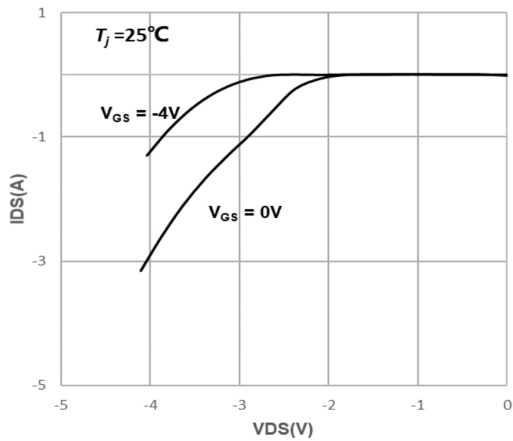
**Fig9. Capacitances vs. Drain-Source Voltage (0-600V)**



**Fig10. Maximum Power Dissipation vs. Case Temperature**

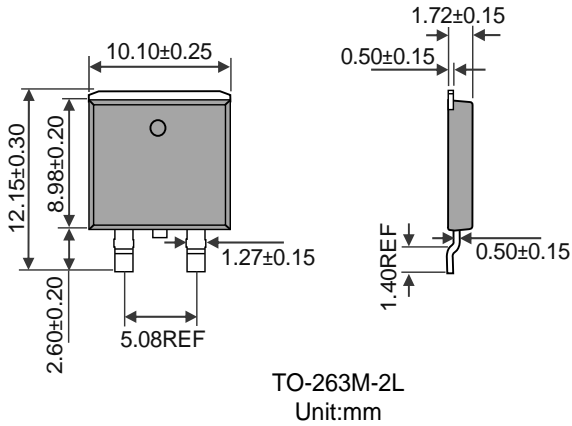


**Fig11. Body Diode Characteristics**

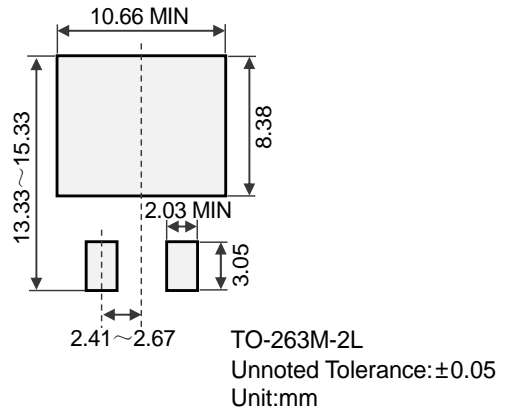


## Package Outline Dimensions & Suggested Solder Pad Layout

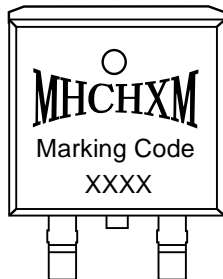
### Package Outline Dimensions



### Suggested Solder Pad Layout



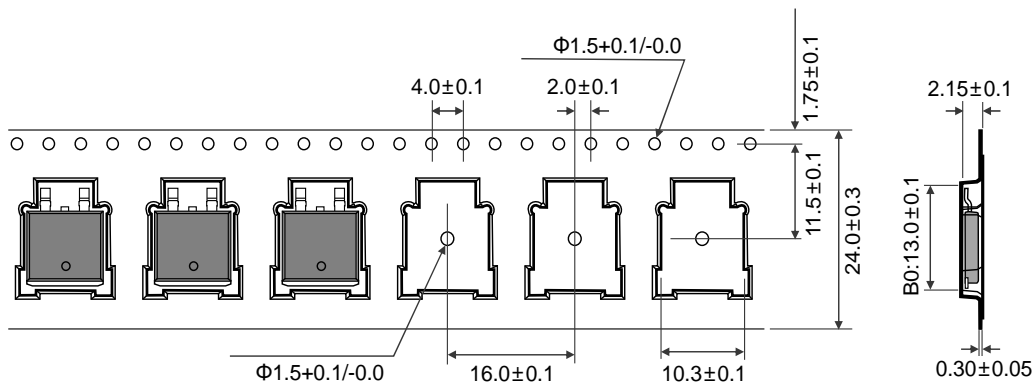
## Marking Information



“MHCHXM”= Product Logo  
 “Marking Code”= The Following  
 “XXXX”= Date Code Marking

Marking Code	Part Number
C65N380M1	HXMC65N380M1

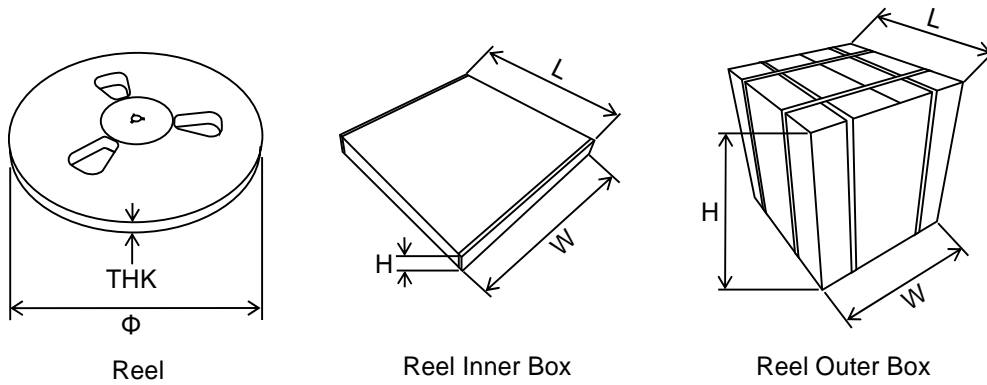
## Reel Tape Dimensions (Dimensions in mm)



**Packing Information**

Packaging	Part Number	Quantity(pcs)	Size(mm)
Reel	Reel	1500	Φ330×THK25
	Inner Box	1500	L355×W335×H35
	Outer Box	15000	L385×W365×H365

**Packaging:Reel**



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